

# Integrated Photonic Devices

<http://ioe.eei.eng.osaka-u.ac.jp/>

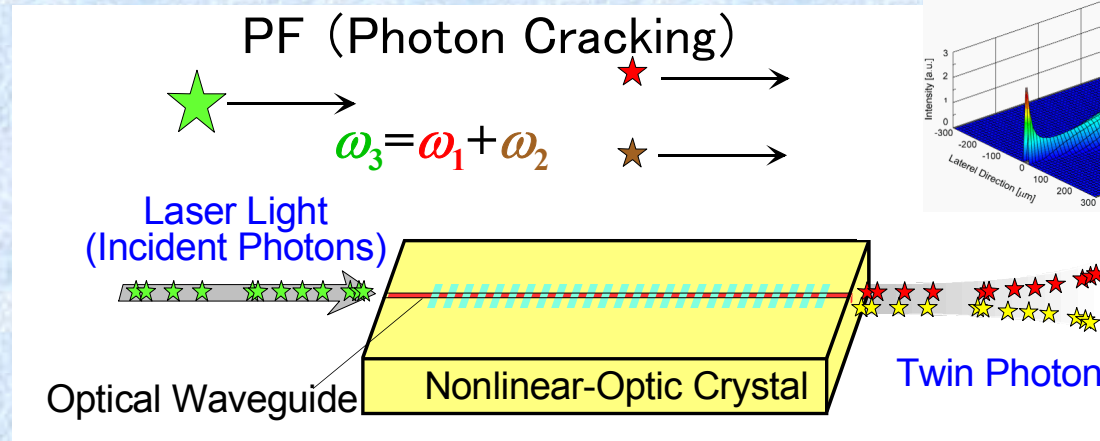
## Advanced Integrated Photonic Devices

- IPD for Optical Network
- IPD for Ultrafast Signal Processing
- Quantum Structure Semiconductor Lasers
- Integrated Photonic Sensors
- Integrated Quantum Photonic Devices

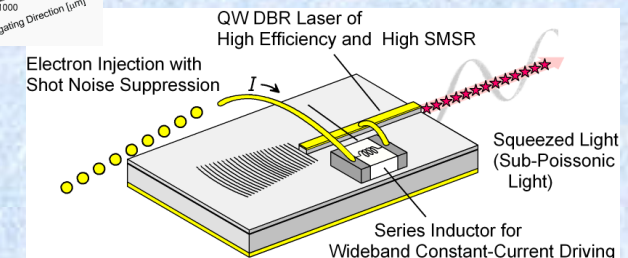
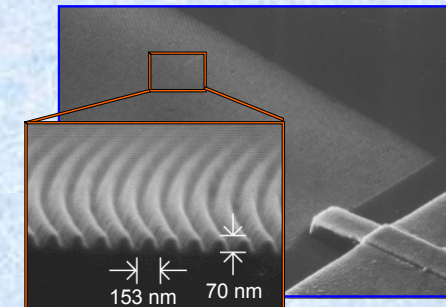


Electron Beam Writing System for Photonics

*Design Theory Simulation Fabrication Technology*  
*Device Implementation • Experimental Demonstration*

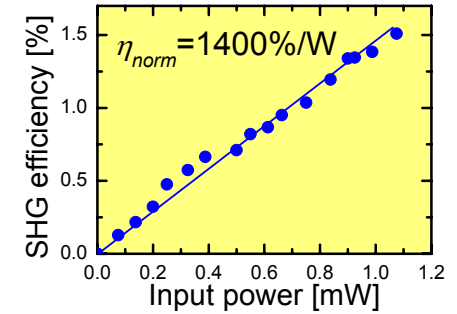
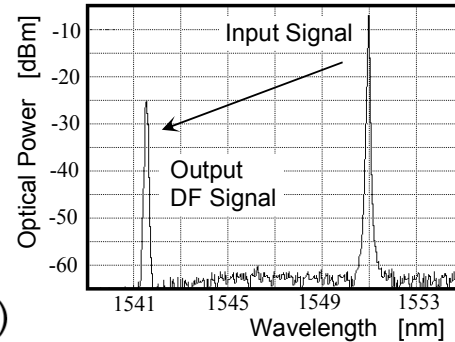
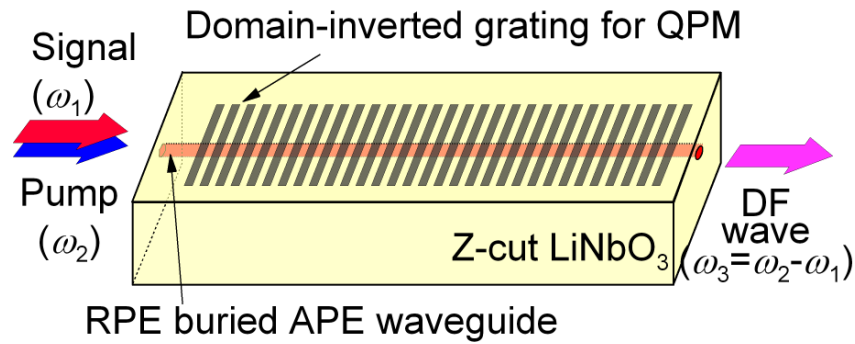


An Example of Quantum Photonic Devices



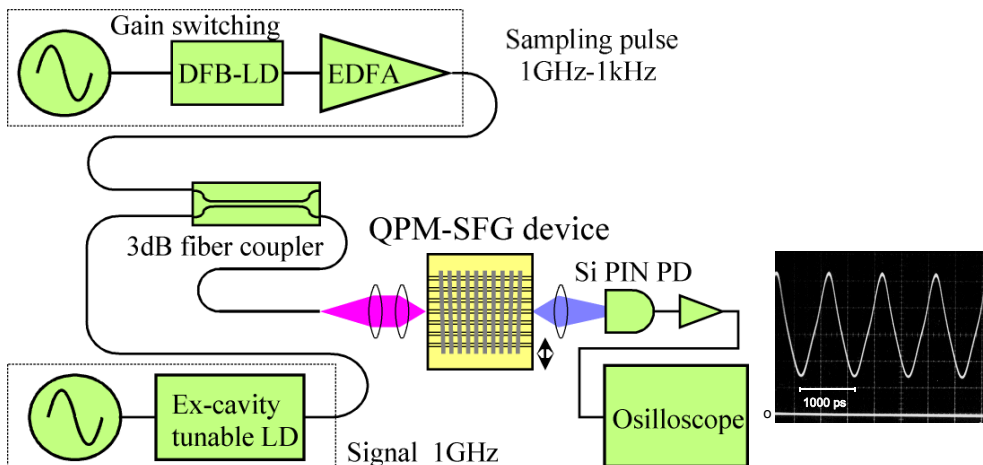
Integrated QW Semiconductor Laser

# Waveguide Nonlinear-Optic Devices



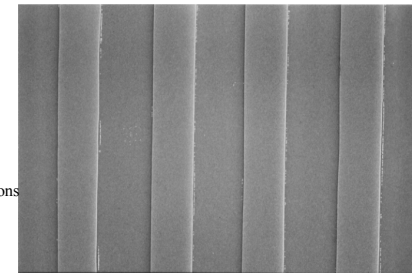
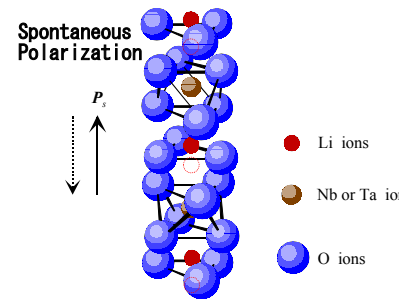
**Top Data Efficiency**

## Wavelength Converters for Photonic Network

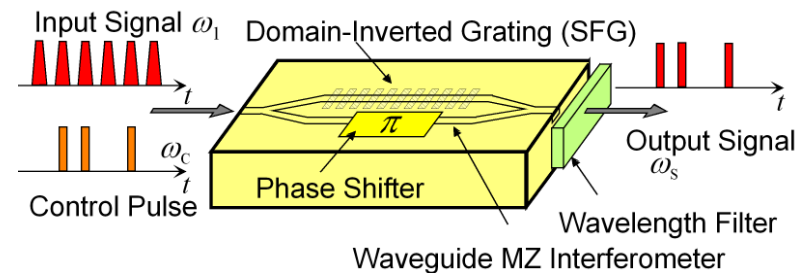


**43%/W  
Highest Efficiency**

**Optical Sampling Device**



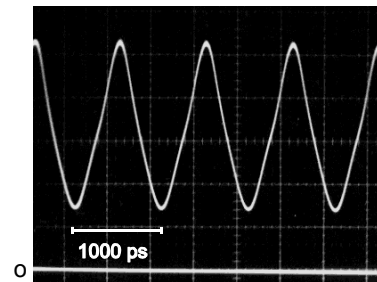
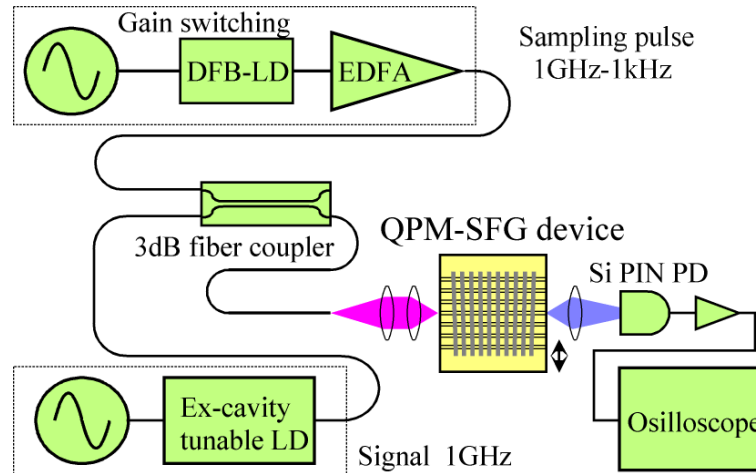
## Domain Inverted Grating for QPM



**Ultrafast Optical Gate Switch**

# Ultrafast Optical-Signal Processing Devices

## SFG Optical Sampling Device



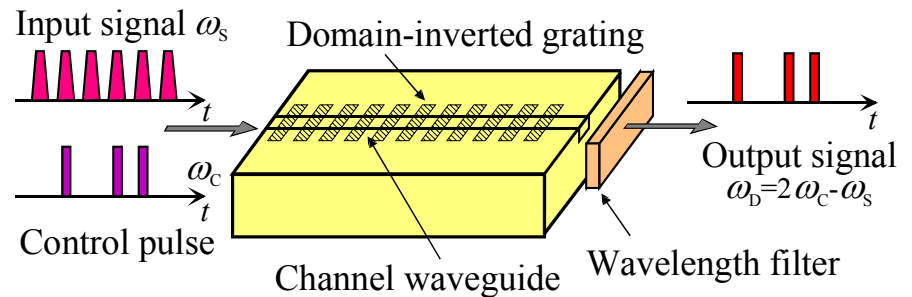
Waveform Observed  
By Optical Sampling

T.Suhara et al. IEEE PTL **11**, 1027, 1999

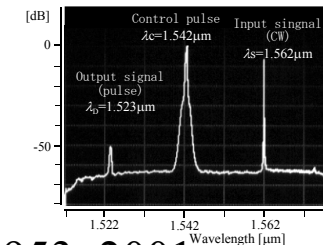
Efficiency  
43%/W

3-order of mag.  
higher  
than with bulk crystal

## SHG/DFG Optical Switching Device

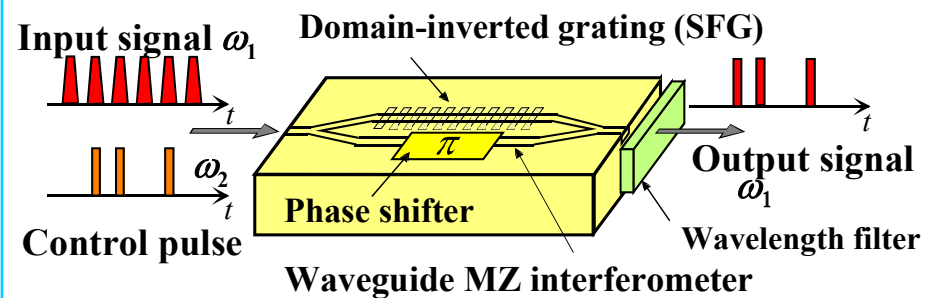


Spectrum of  
Output Waves



H.Ishizuki et al. OQE **33**, 953, 2001

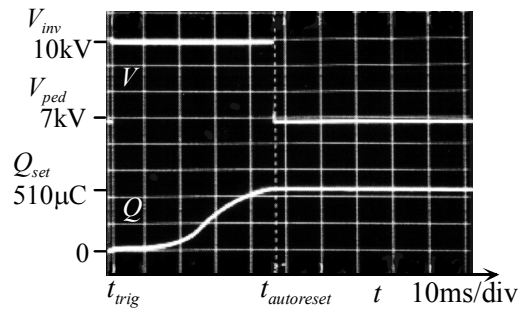
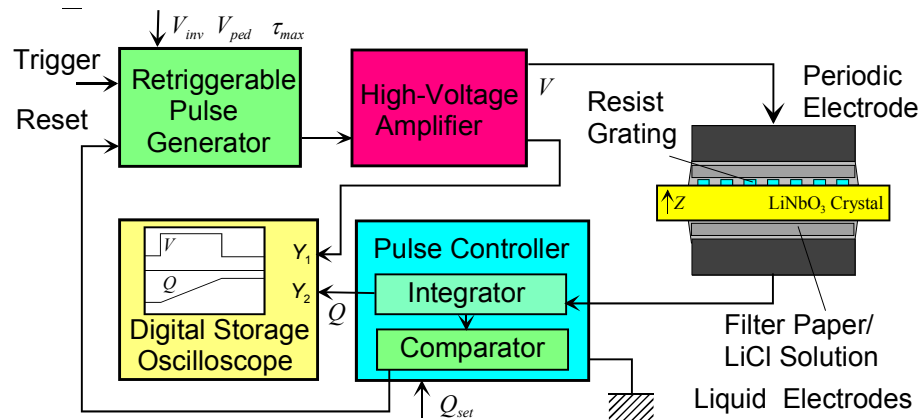
## SFG Interferometer Gate Switch



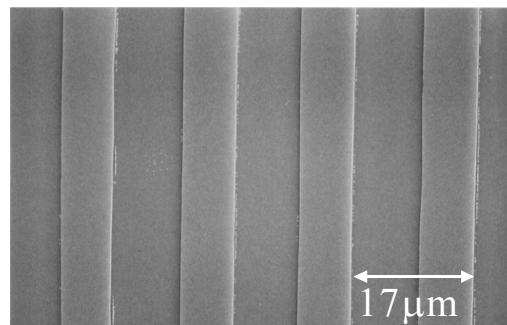
T.Suhara et al. IEEE PTL **13**, 1203, 2001

# Formation of Domain-Inverted Grating for QPM

## Voltage Pulse Application using Liquid Electrodes

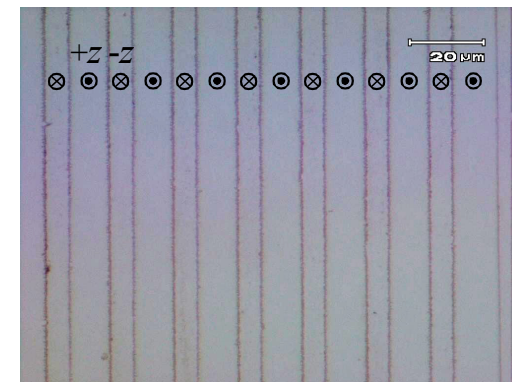
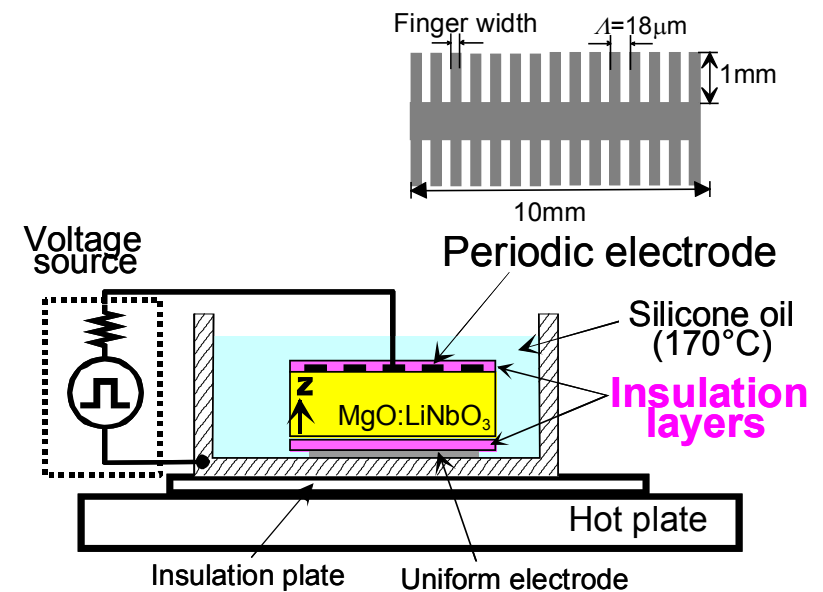


Voltage /Charge Traces



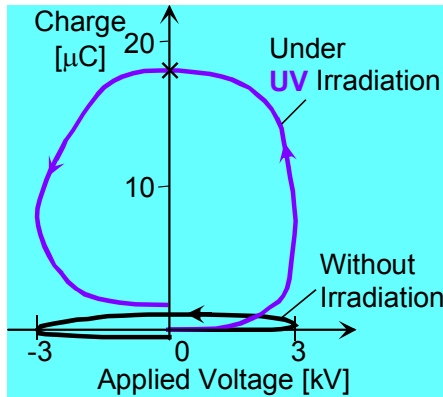
SEM Microphotograph of Domain-Inverted Grating

## Voltage Pulse Application using Metal Electrodes



N.Horikawa, T. Tsubouchi, M.Fujimura and T.Suhara, Jpn. J. Appl. Phys., 46, 5178, 2007.

# QPM Grating Formation in MgO:LiNbO<sub>3</sub> Crystal

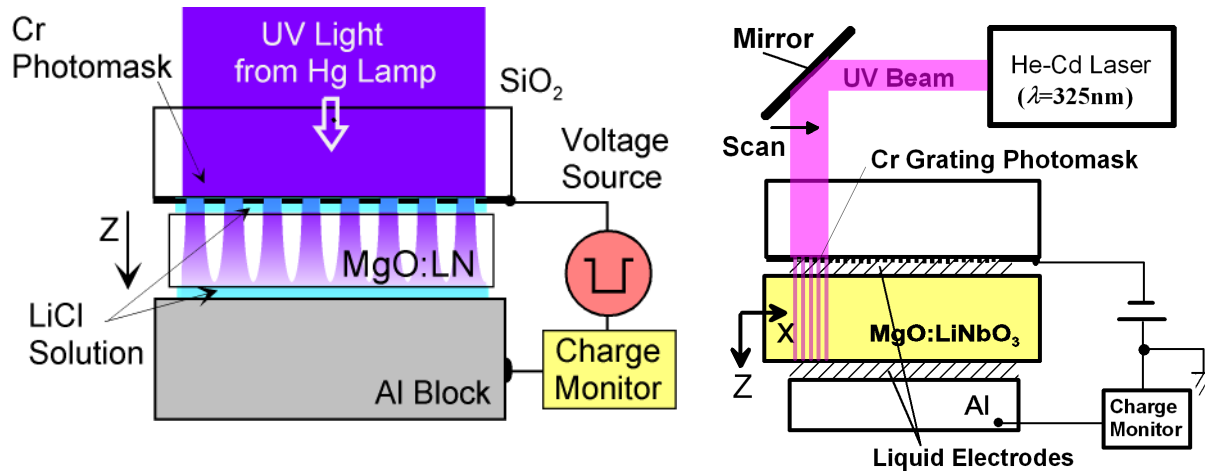
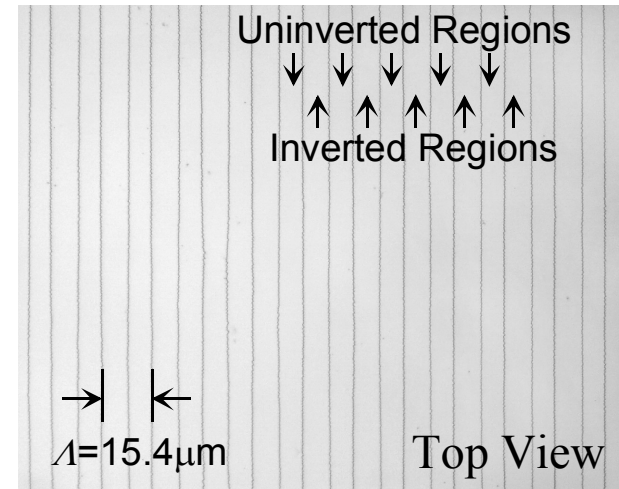


**MgO:LiNbO<sub>3</sub>**  
**PR damage resistant**

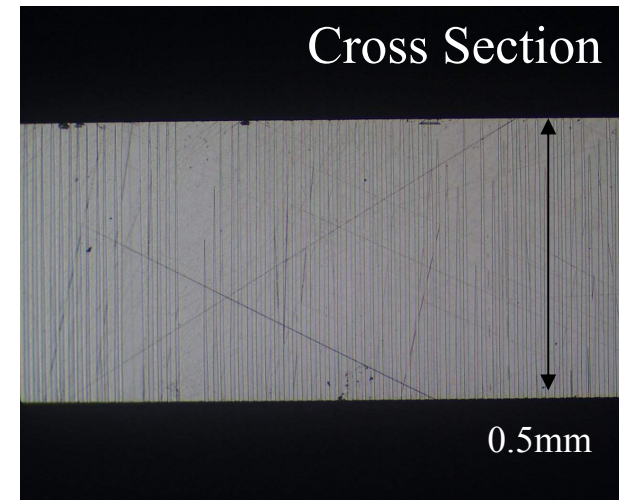
**UV Irradiation**  
 Reduces  
 Eff. Coercive Field

## Ferroelectric Hysteresis Loop

Room Temperature Resistless Process



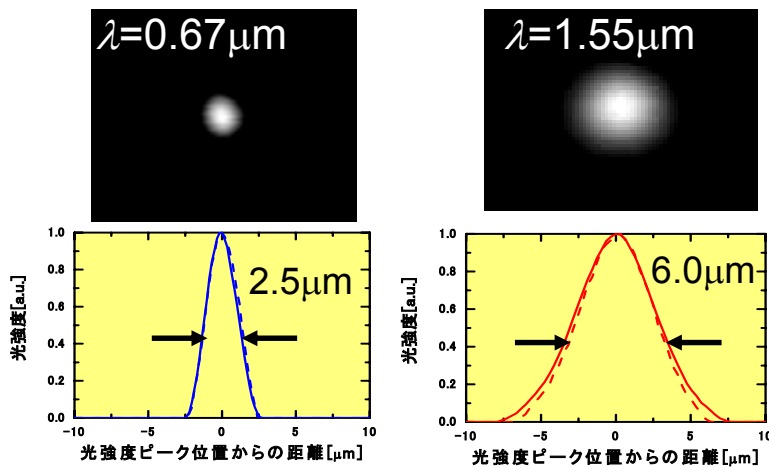
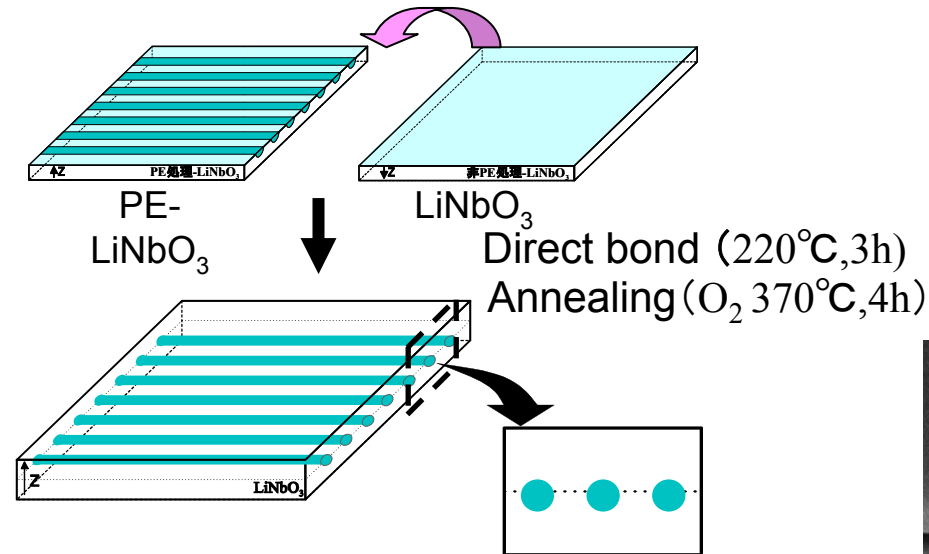
## Formation of QPM Grating



M.Fujimura, T.Sohmura and  
 T.Suhara EL. 39, 719, 2003

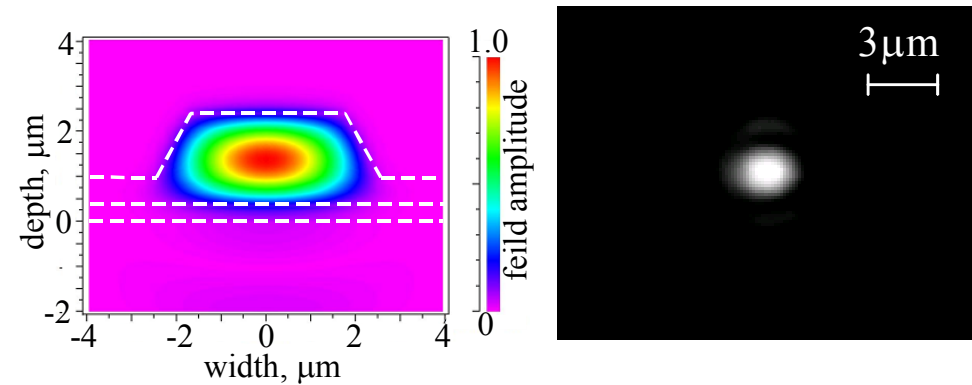
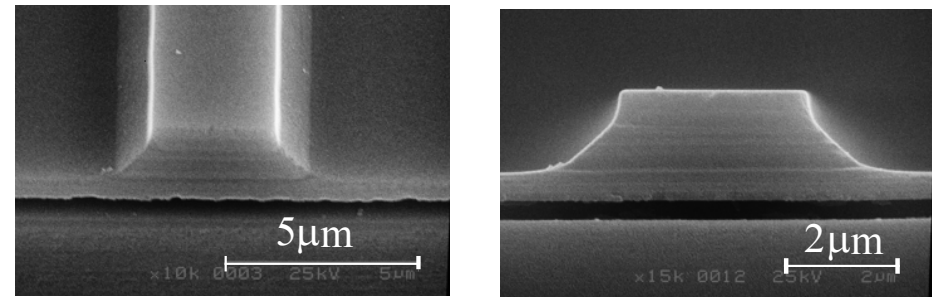
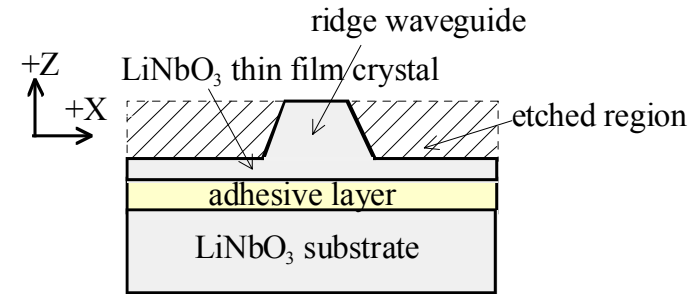
# Fabrication of WG of strong confinement

## Buried APE WG fabrication by direct bonding



M.Fujimura et al. EL 44, 856 2008

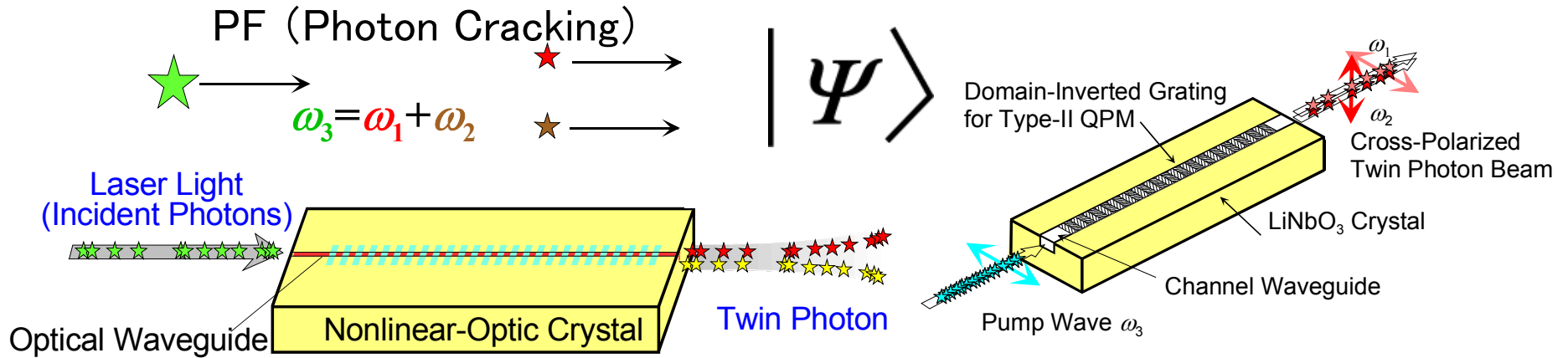
## Ridge WG fabrication by PE accelerated chemical etching



T.Takaoka et al. EL 45, 940 2009

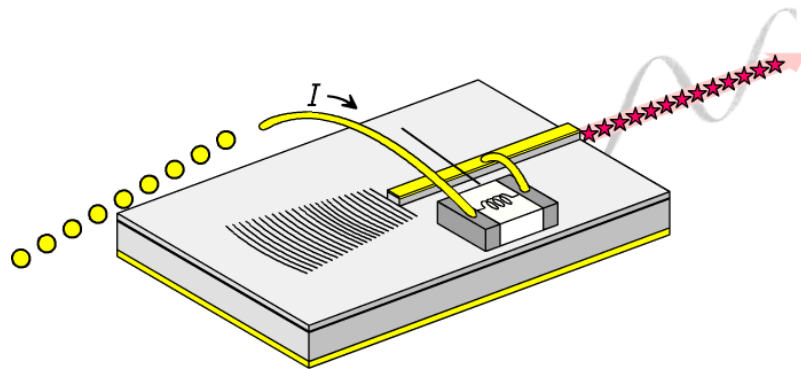
# Quantum Photonic Devices

## Efficient Integrated Photonic Devices for Quantum Optic Function



Correlated Twin-Photon Generation

- Entangled Photon Generation
- Single Photon Generation



Squeezed Light Semiconductor Laser

Applications

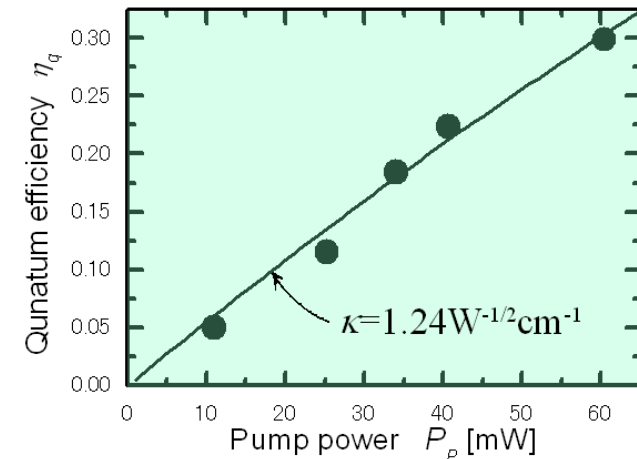
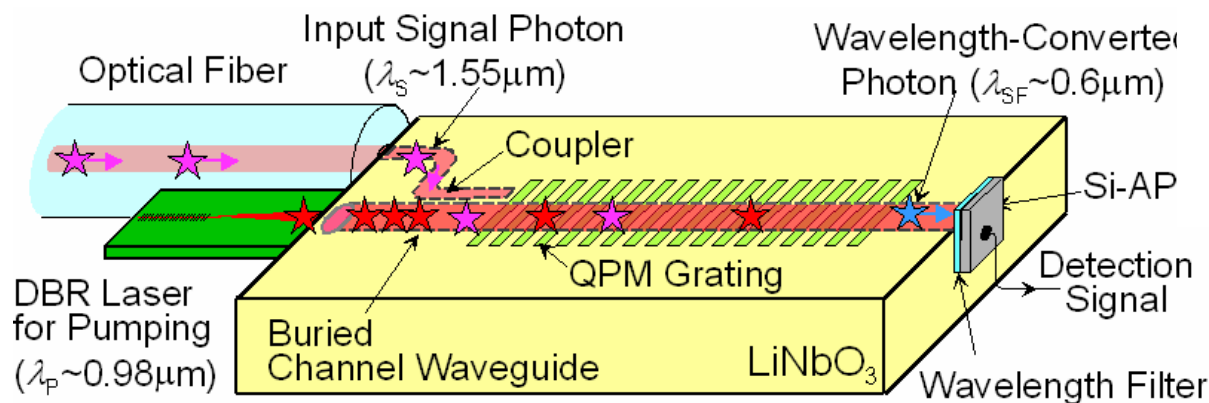
- Quantum Information
- Quantum Cryptography
- Quantum Computing
- Quantum Photonic Sensing

# QPM WG SFG upconversion device for single photon detection

QIT Photon transmission through fiber network  
**Telecom (1.3, 1.5 $\mu\text{m}$ ) band Single photon detector**

InGaAs-APD involve drawbacks

**SFG upconversion to visible and detection by Si-APD**



**$\eta \sim 30\%$  @  $P_p = 60 \text{mW}$**

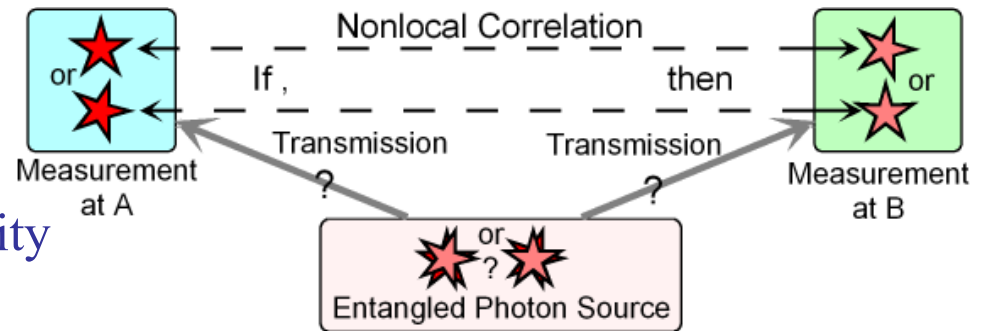


# WG QPM Entangled Twin Photon Generation Devices

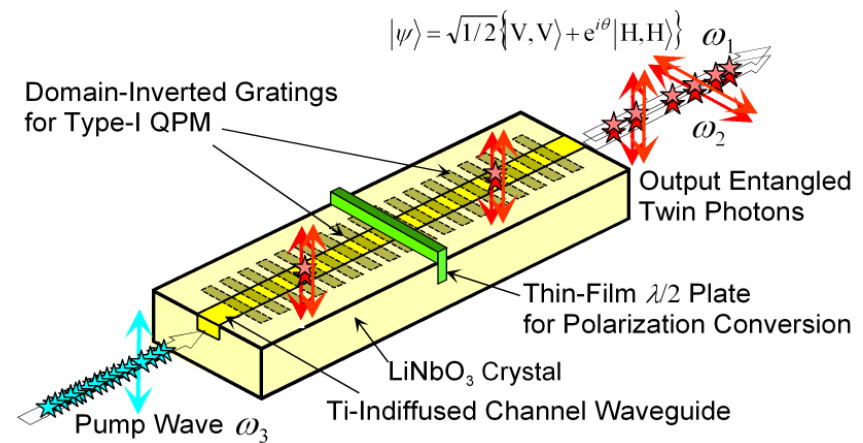
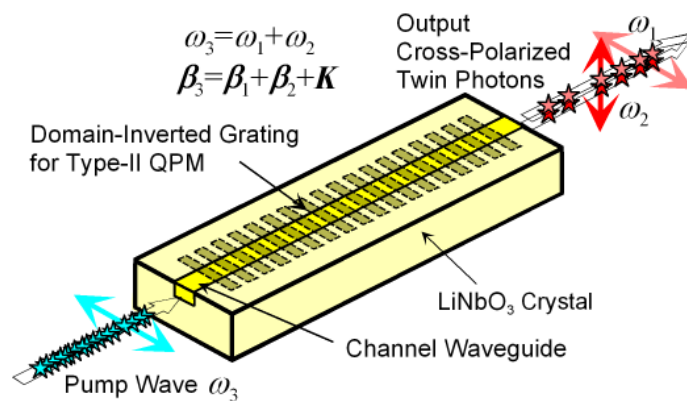
## QPM Waveguide NLO Devices for Quantum Information Processing Q-Cryptography, Q-Teleportation, Q-Interface, ...

### Quantum Entangled Twin Photons

high efficiency, wavelength flexibility  
Integration compatibility



### Key Device for QIT



T.Suhara et al. IEEE PTL **19**, p.1093,2007.

J.Kawashima et al., IEEE PTL., **21**, p.566, 2009.

# Quantum theory analysis of TPG

## Quantum coupled mode eq (H.P.)

$$\frac{d}{dz} a_1(z) = i\kappa A_3 a_2^\dagger(z) \exp(i2\Delta z)$$

$$\frac{d}{dz} a_2(z) = i\kappa A_3 a_1^\dagger(z) \exp(i2\Delta z)$$



## Unitary transformation of state (S.P.)

$$|\phi(L)\rangle = T(L)|0,0\rangle = \exp(-iHL)|0,0\rangle$$

$$= \sum_{n=0}^{\infty} \frac{1}{n!} (-iHL)^n |0,0\rangle$$

$$H = i\{a_1^\dagger(\Gamma e^{i\phi} a_2^\dagger - i\Delta a_1) - (\Gamma e^{-i\phi} a_1 + i\Delta a_2^\dagger) a_2\}$$

$$|\phi(L)\rangle = \sum_{n=0}^{\infty} \sqrt{1-|r|^2} r^n |n,n\rangle$$

$$r = \frac{e^{i\phi} (\Gamma/\gamma) \sinh \gamma L}{\cosh \gamma L + i(\Delta/\gamma) \sinh \gamma L}$$

$$\langle N_1(L) \rangle = \langle N_2(L) \rangle = \sinh^2 \Gamma L \{ \sin \Delta L / \Delta L \}^2$$

$$P_{out1} = \hbar \omega_1 \int \langle N_1(L) \rangle (d\omega_1 / 2\pi) \text{ in QPM bandwidth}$$

### Photon CCR

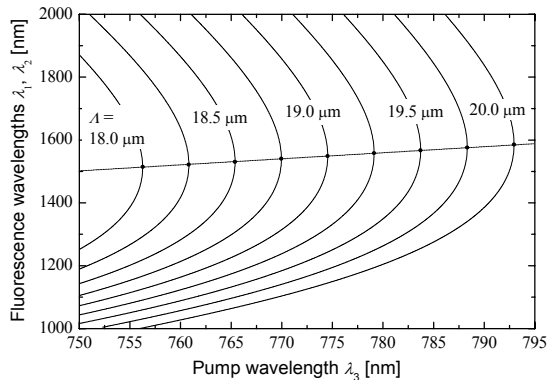
$$P_c(\tau) \propto \text{rect}\left(2 \frac{\delta\omega}{2\pi} \tau\right)$$

### Correlation time

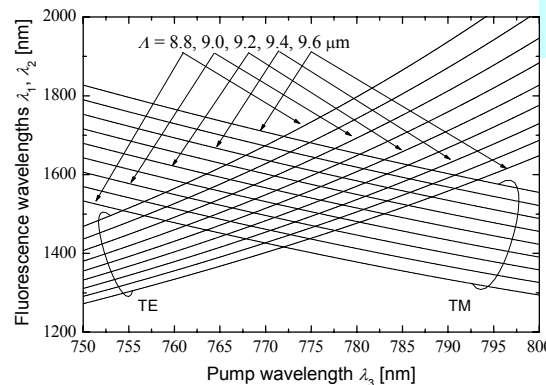
$$\tau_c = (\delta\omega / 2\pi)^{-1} = |n_1 - n_2| L / c$$

$$\langle [\Delta \{N_1(L) - N_2(L)\}]^2 \rangle = 0$$

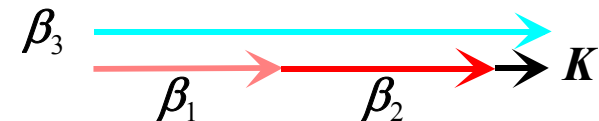
complete correlation



TM → TM+TM Type-I QPM

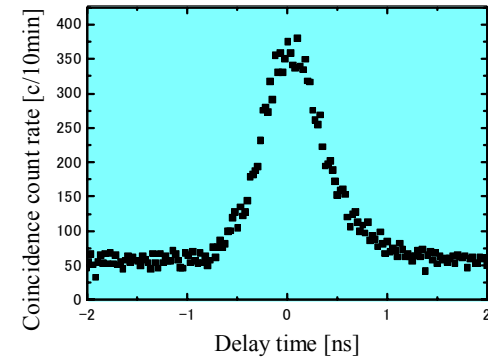
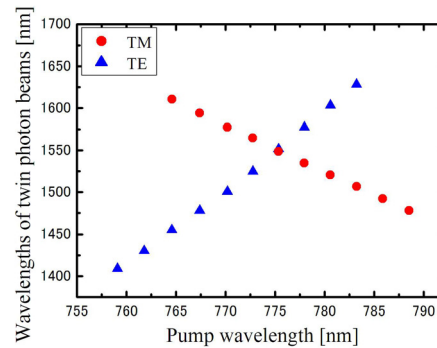
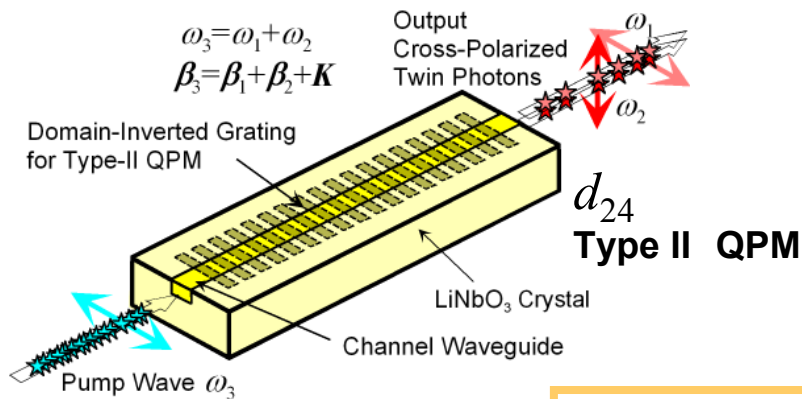


TE → TM+TE Type-II QPM



T.Suhara et al. IEEE JQE, **41**, 1203, 2005; **42**, 777, 2006

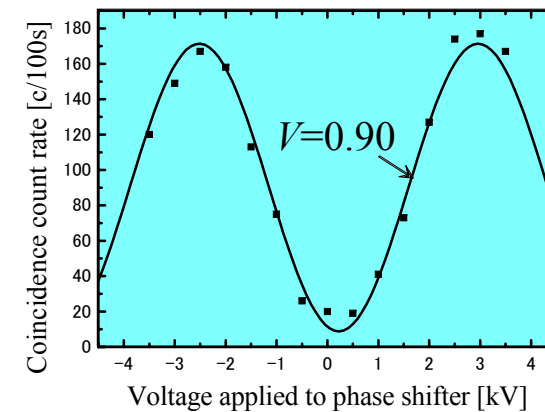
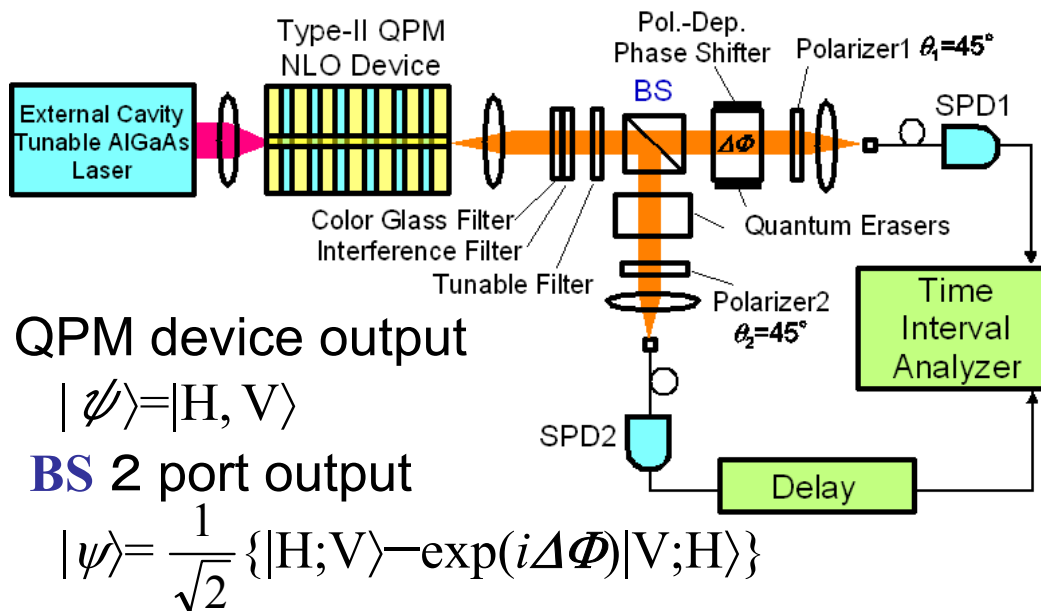
# Type-II QPM Cross-Polarized TPG Device



$$\eta \sim 3 \times 10^{-10}$$

Photon Correlation

T.Nosaka et al. IEEE PTL, **18**, 1, p.124, 2006

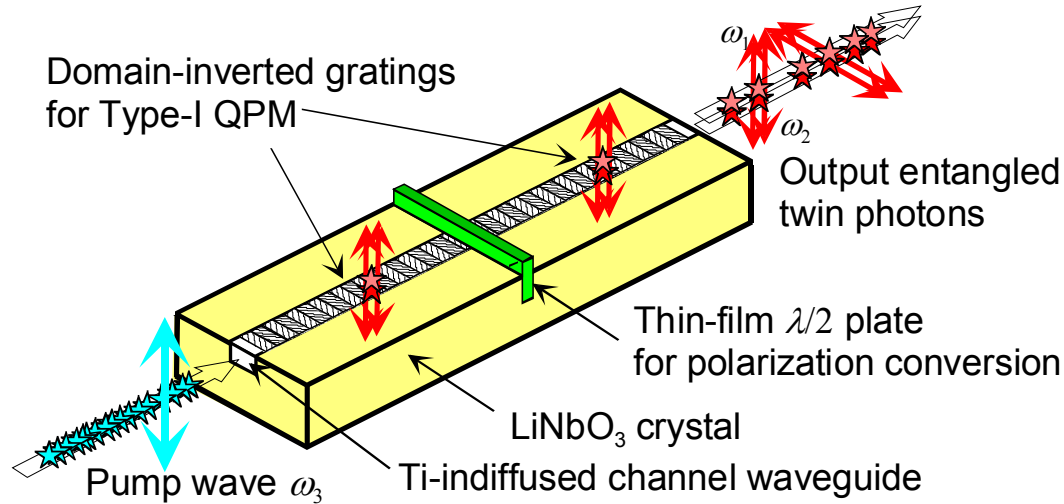


Quantum Interference

Polarization Entangled TPG

T.Suhara et al. IEEE PTL, **19**, 1093, 2007

# Type I QPM Polarization-Entangled TPG Device



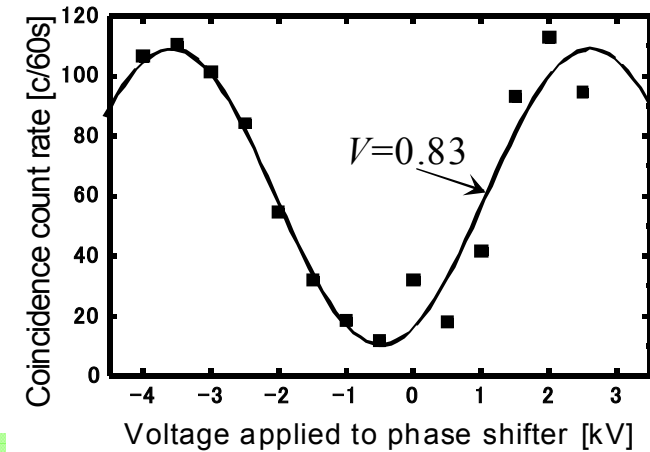
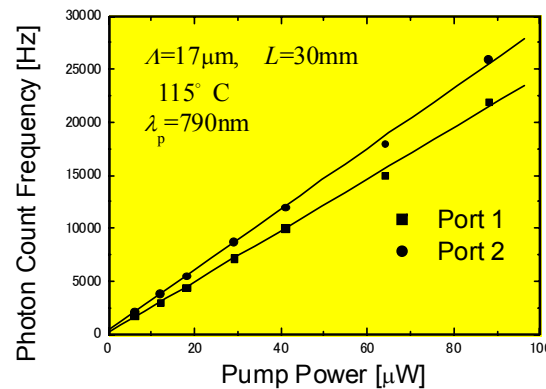
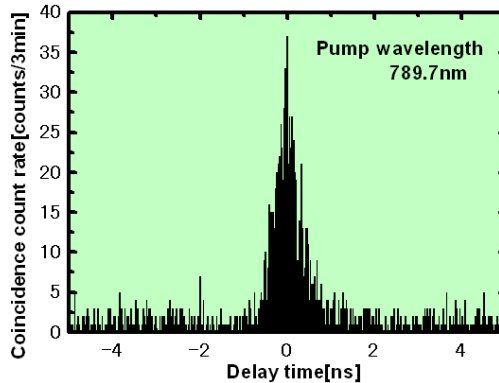
QPM device output

$$|\psi\rangle = \frac{1}{\sqrt{2}} \{ |H,H\rangle + \exp(i\Phi_0) |V,V\rangle \}$$

BS output 1,2 state

$$|\psi\rangle = \frac{1}{\sqrt{2}} \{ |H,H\rangle - \exp(i\Phi) |V,V\rangle \}$$

Quantum entangled state

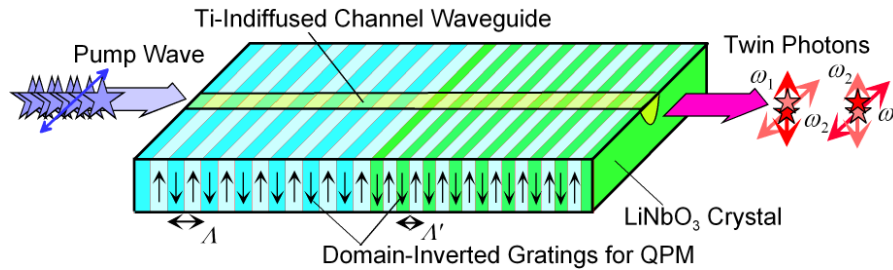


Photon correlation

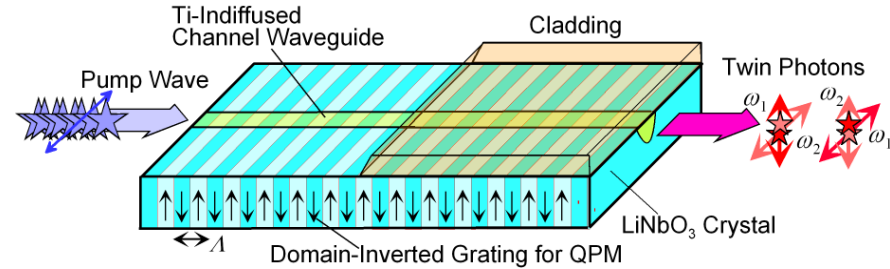
$\eta = 2.4 \times 10^{-7}$  (theory  $1.7 \times 10^{-6}$ )  
**High Efficiency** higher than Type II QPM by 3 orders of magnitude

Quantum Interference demonstrating entangled TPG

# QPM WG Devices for Generation of Postselection-Free Polarization-Entangled Twin Photons



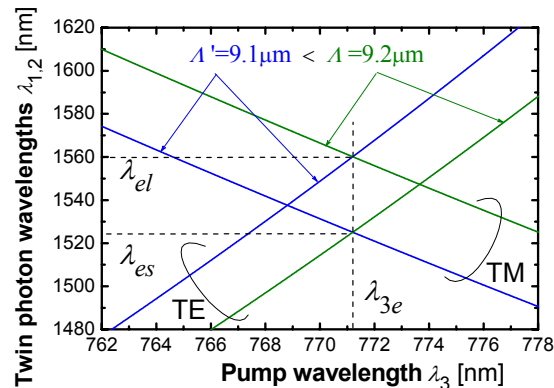
(a) Biperiod type



(b) Clad/Unclad type

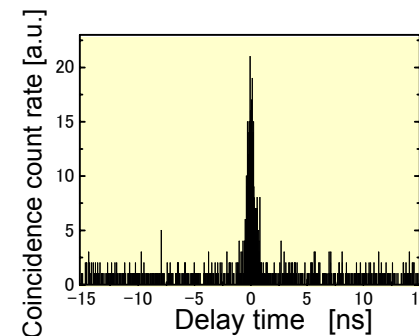
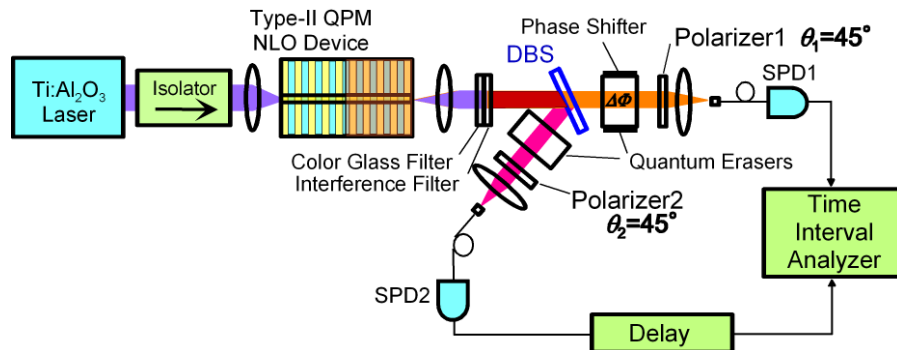
Output state: 
$$|\psi\rangle = \frac{1}{\sqrt{2}} \{ |H, V\rangle + \exp(i\Phi_0) |V, H\rangle \}$$

$$\lambda_{el} \lambda_{es} \qquad \qquad \lambda_{el} \lambda_{es}$$

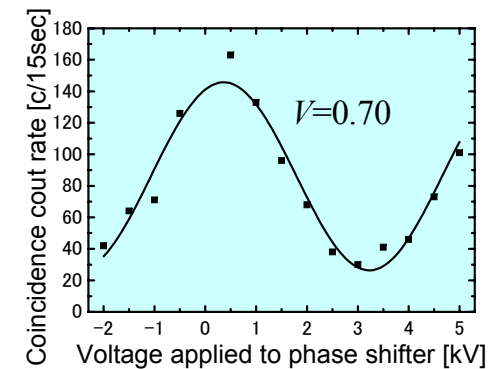


completely separated by DBS

**Postselection-free two- $\lambda$  polarization-entangled twin photons without spurious photon**

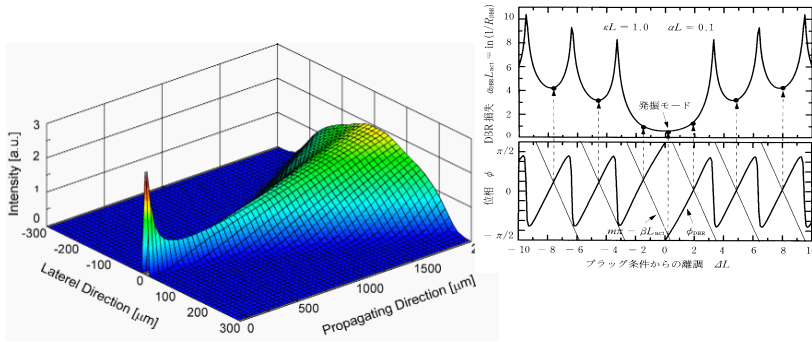


photon correlation

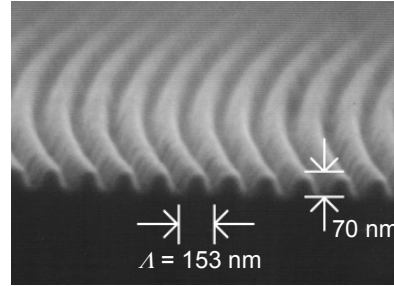


Quantum interference

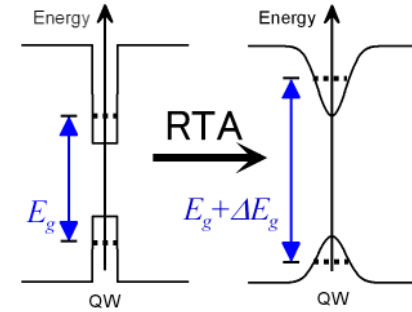
# Integrated Semiconductor Lasers



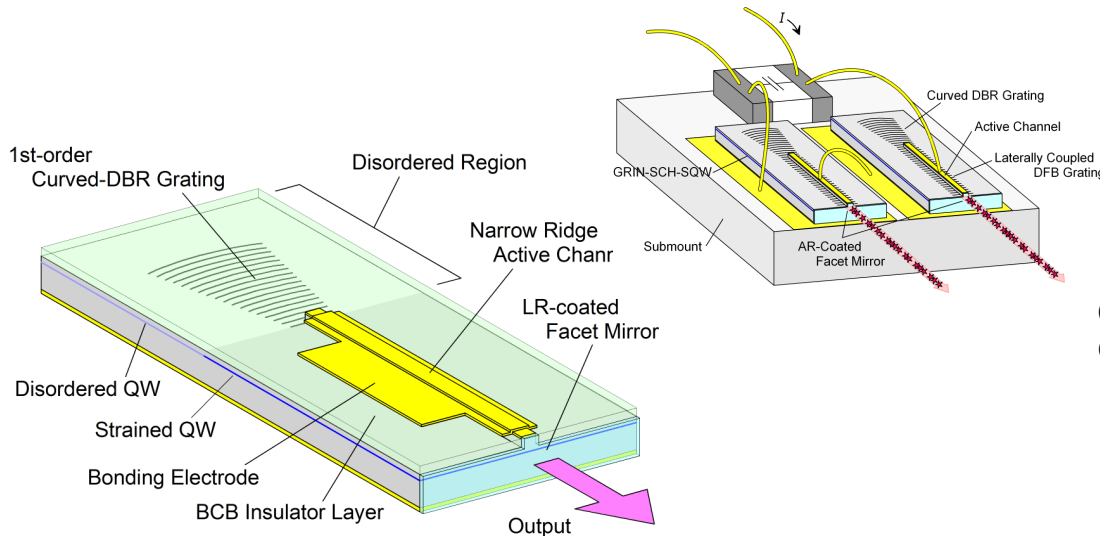
DFB/DBR Laser Simulation



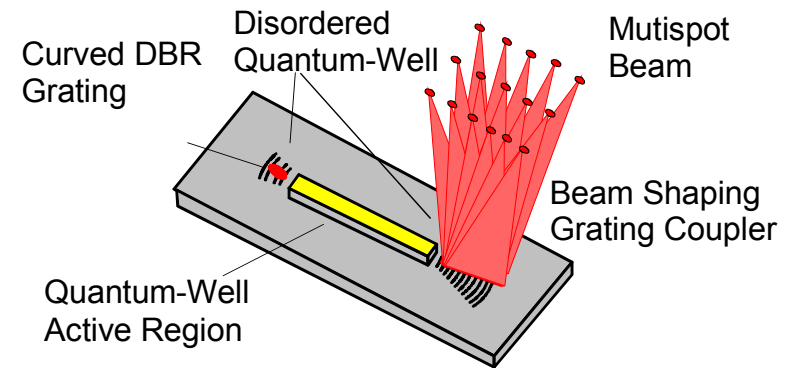
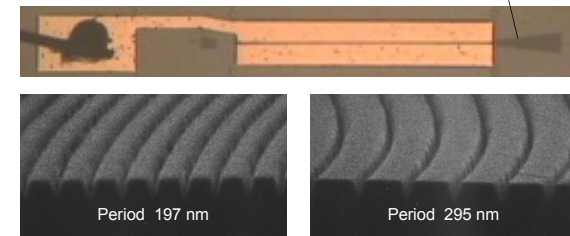
EB Fabrication of Nano Gratings



Selective Disordering of Quantum Well



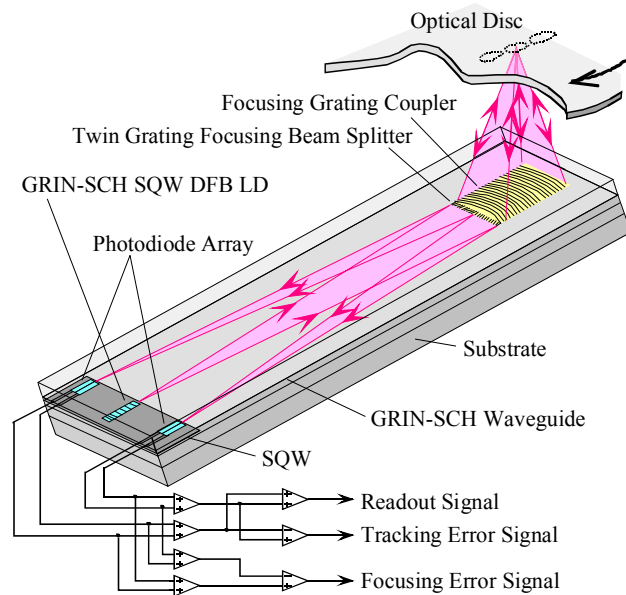
Integrated Semiconductor Lasers for Photonic Network and Quantum-Information



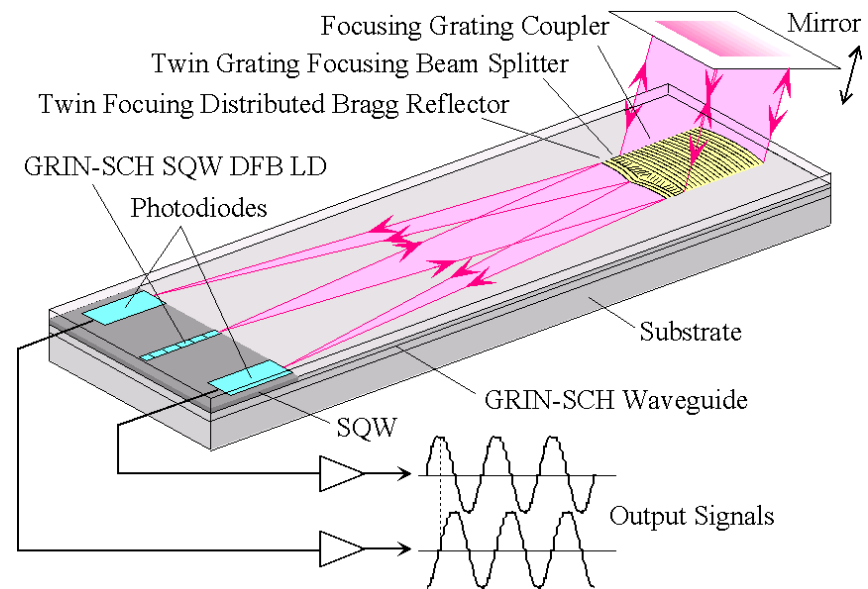
Integrated Semiconductor Lasers for Bio-Sensing

# Monolithic Integrated-Optic Sensor Devices

## Implementation of IO Sensor Devices by Integration of DFB/DBR Laser, Wavefront Conversion Elements and Photodetectors

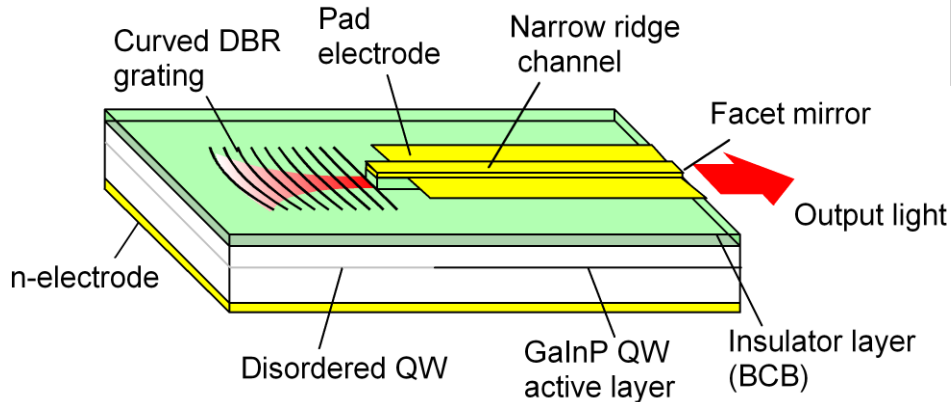
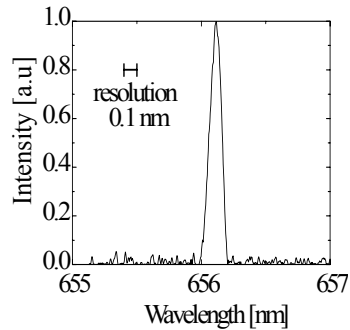


**Monolithic Integrated-Optic Disc Pickup Head**



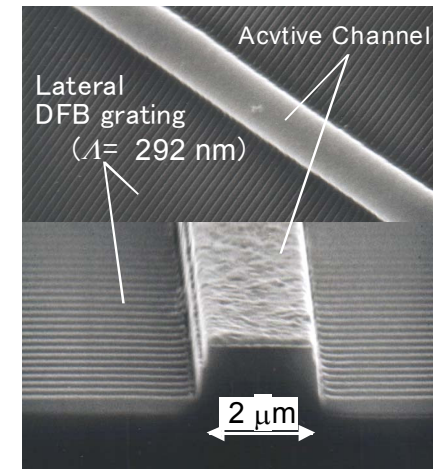
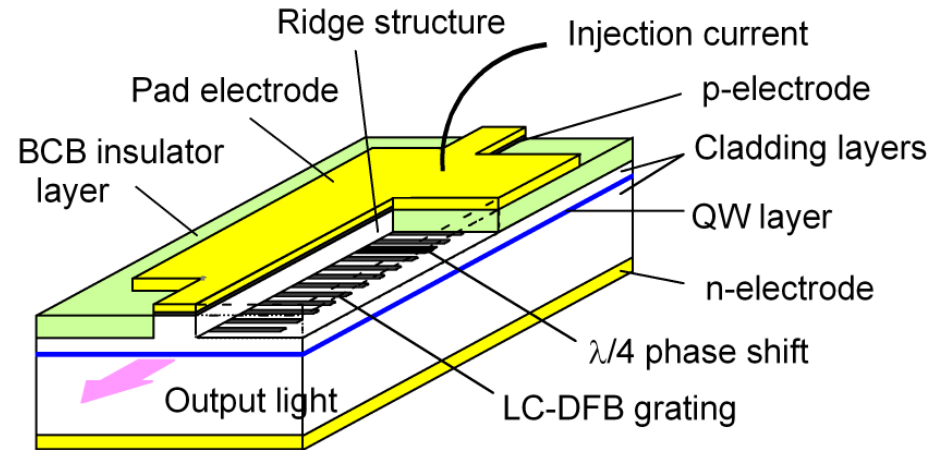
**Monolithic Integrated-Optic Interferometer Position/Displacement Sensor**

# Design Fabrication and Improvement of Novel Semiconductor Lasers



**Red light** emission DBR Laser  
**44mW output**

for integrated optical memory  
 integrated biosensing devices

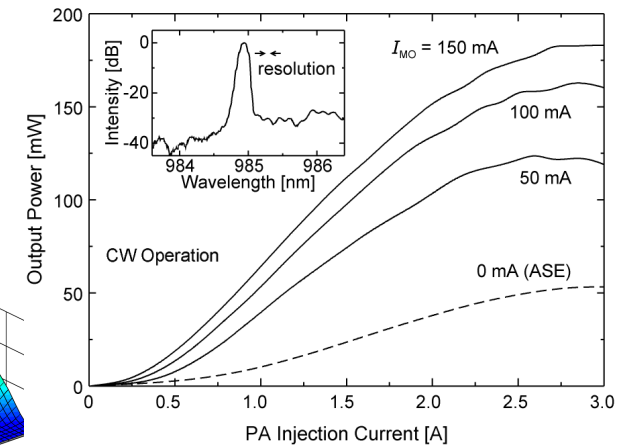
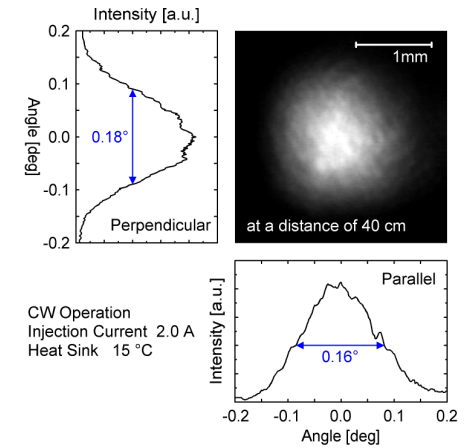
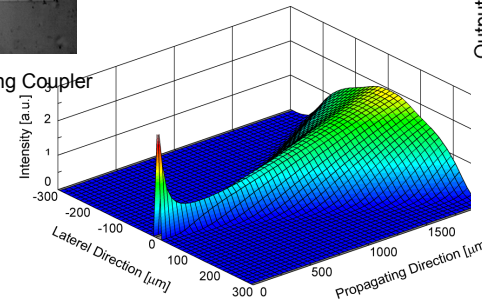
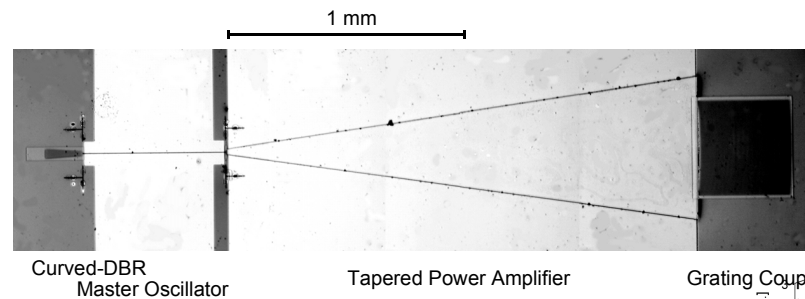
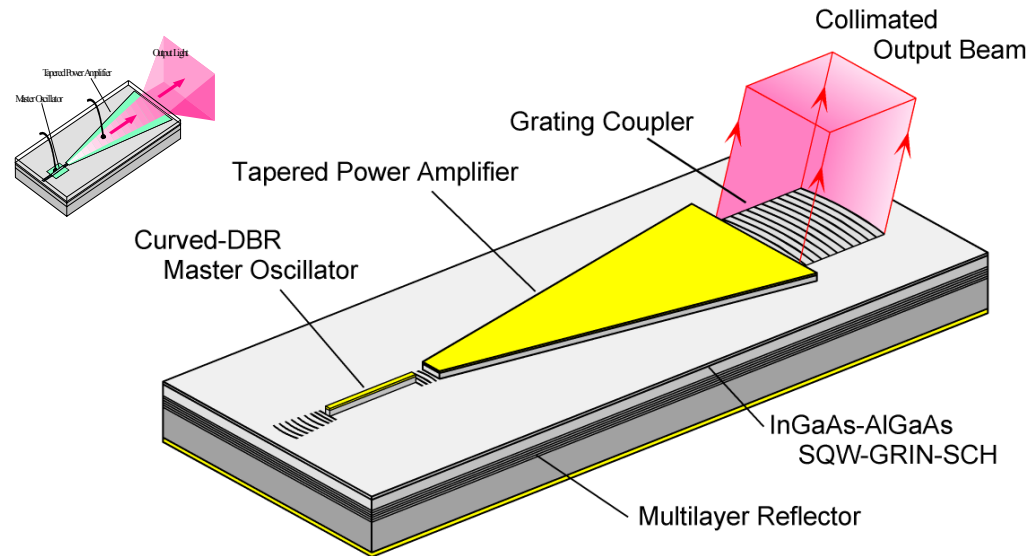


**Lateral Coupling** DFB Laser  
 19mW output , 46dB SMSR

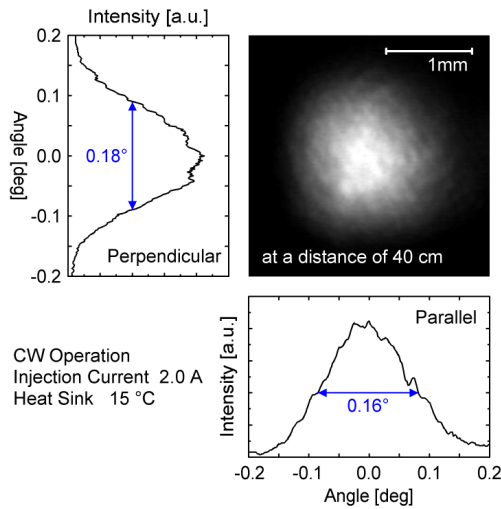
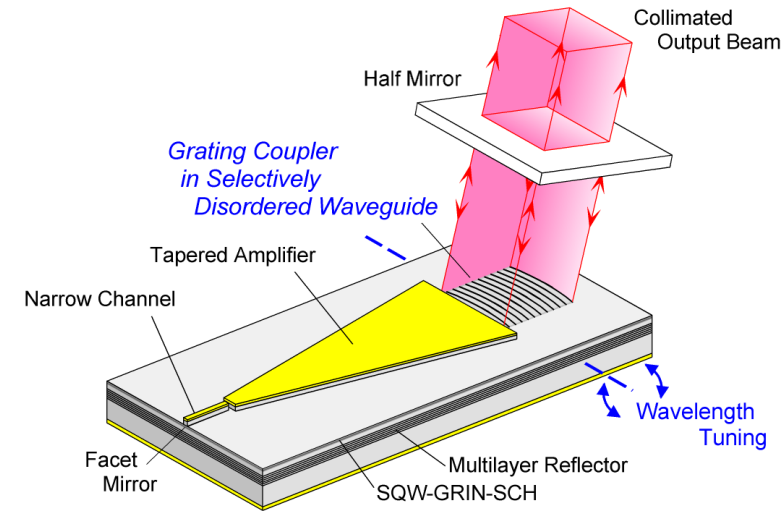


# Integrated High-Power High Coherence Semiconductor Lasers

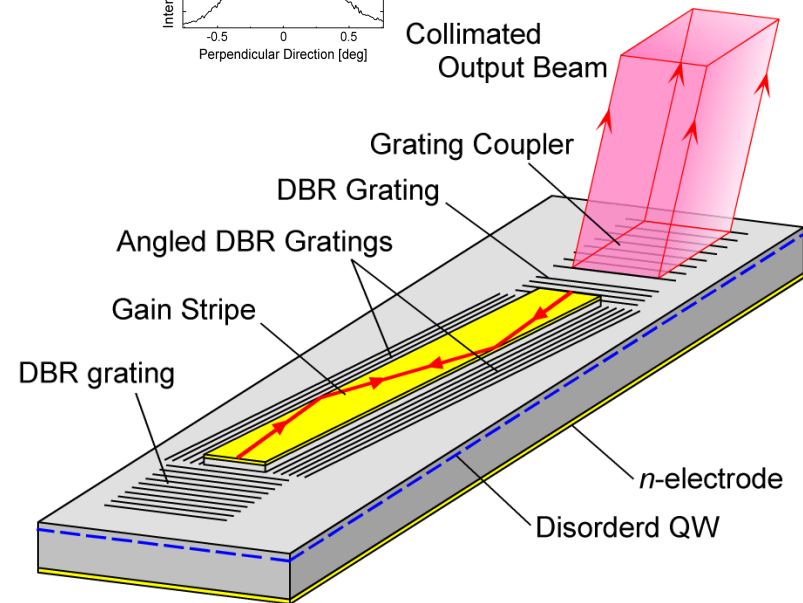
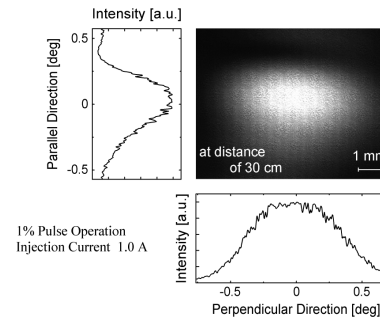
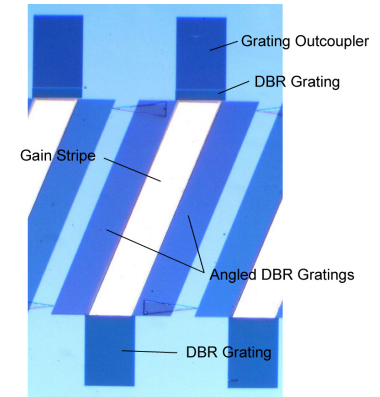
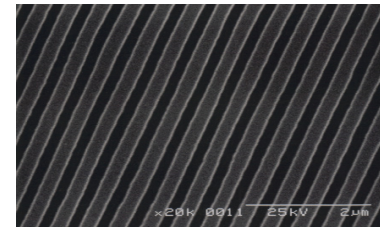
## Master Oscillator Power Amplifier with integrated Outcoupler



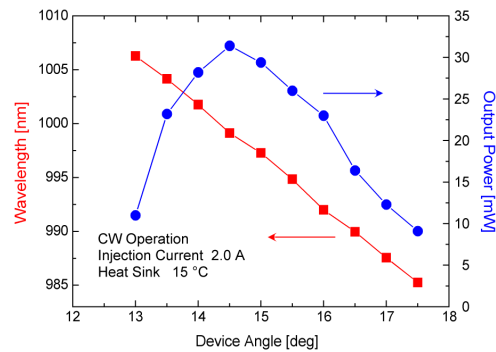
# Integrated High-Power High Coherence Semiconductor Lasers



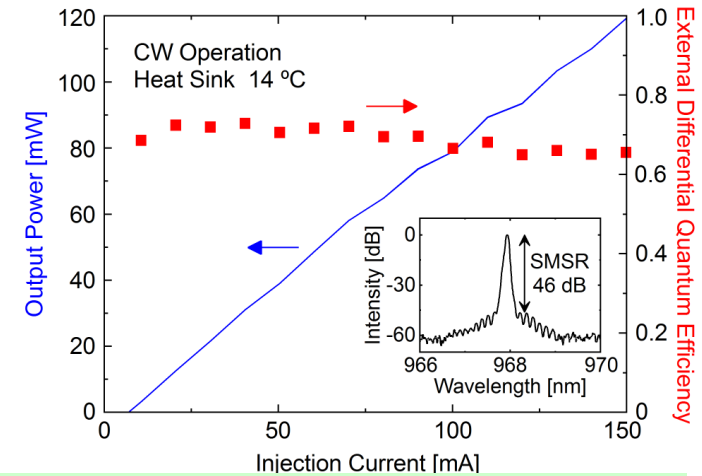
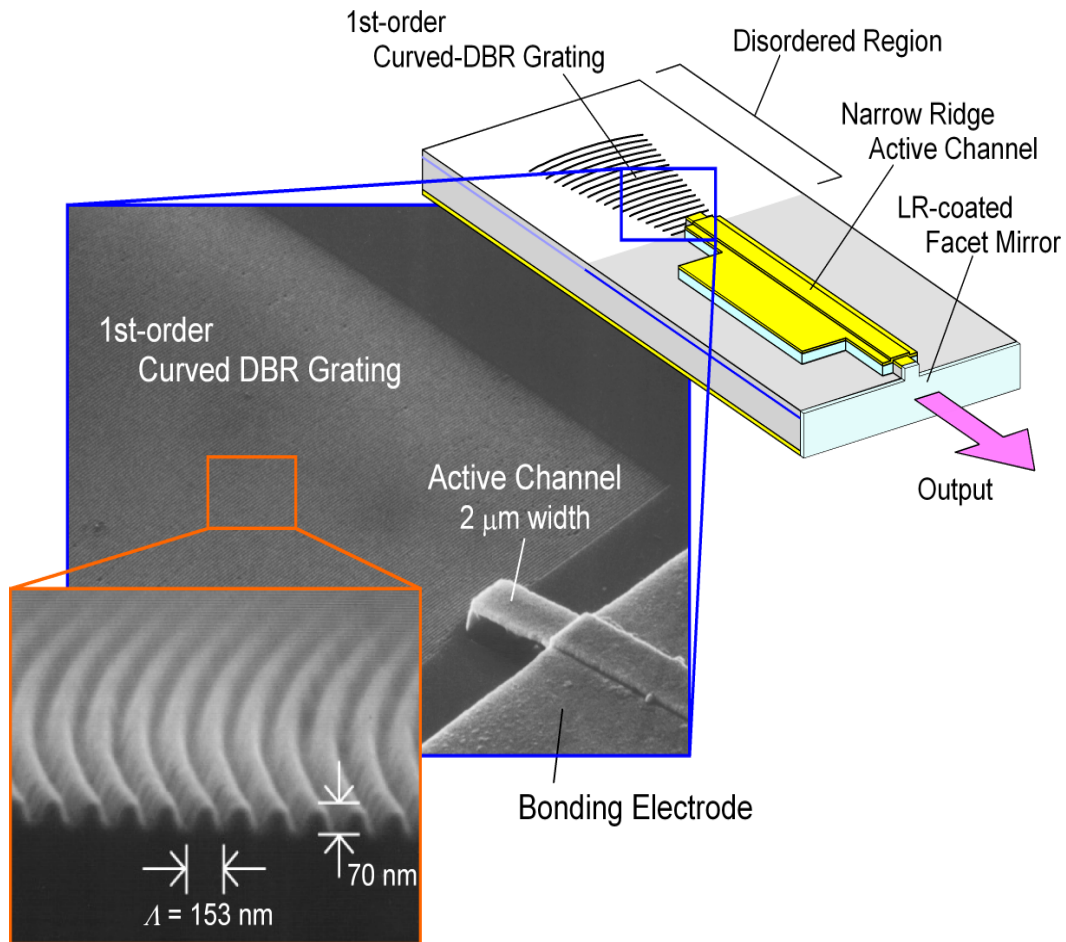
**Extended Cavity Tunable Laser**



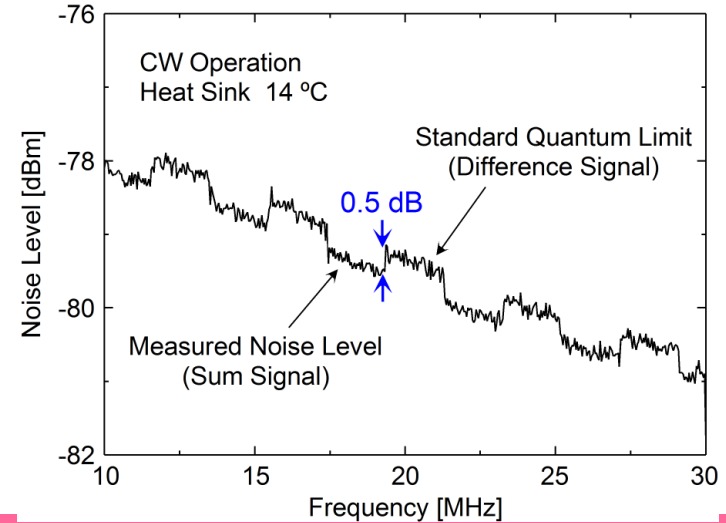
**Broad-Area DBR Laser**



# InGaAs QW DBR Laser for Squeezed Light Generation



$$I_{th} = 7 \text{ mA} \quad \eta_d \sim 0.63 \quad \text{Max } I/I_{th} = 21$$



Generation of Squeezed Light

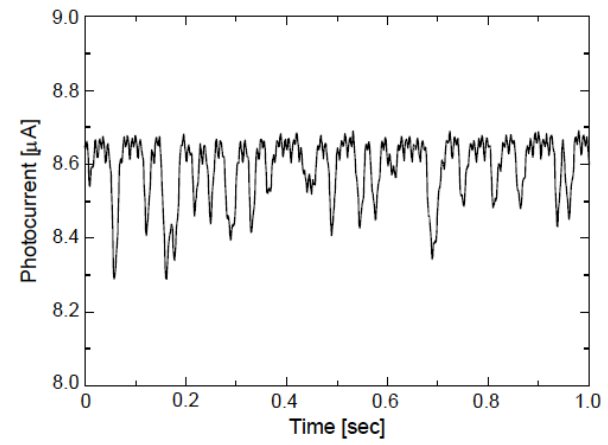
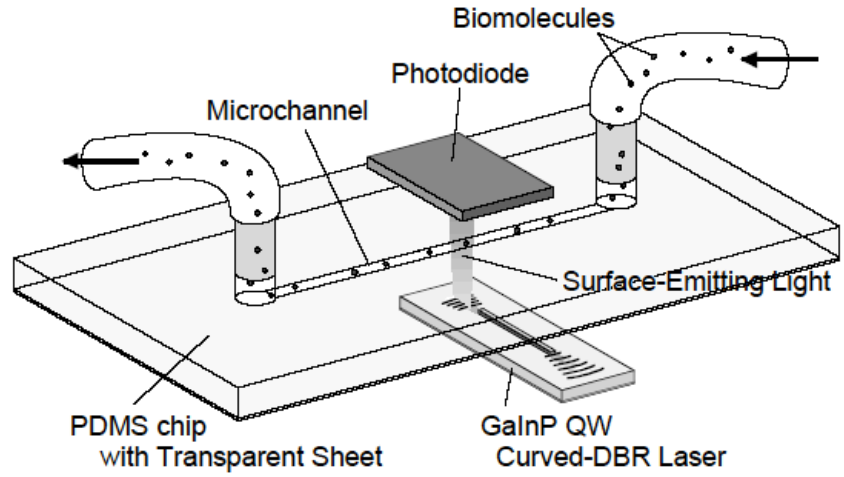
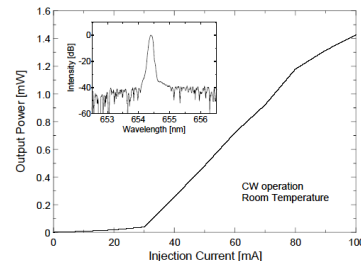
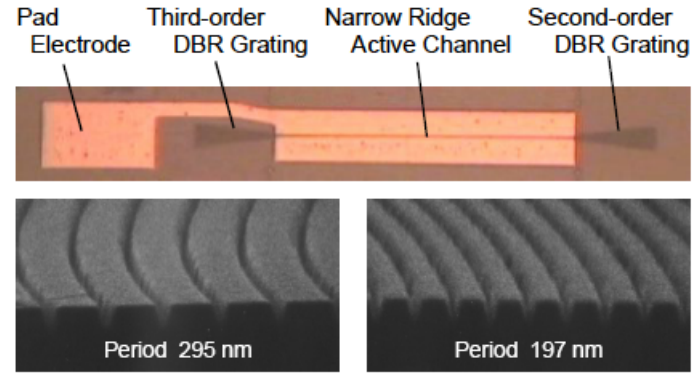
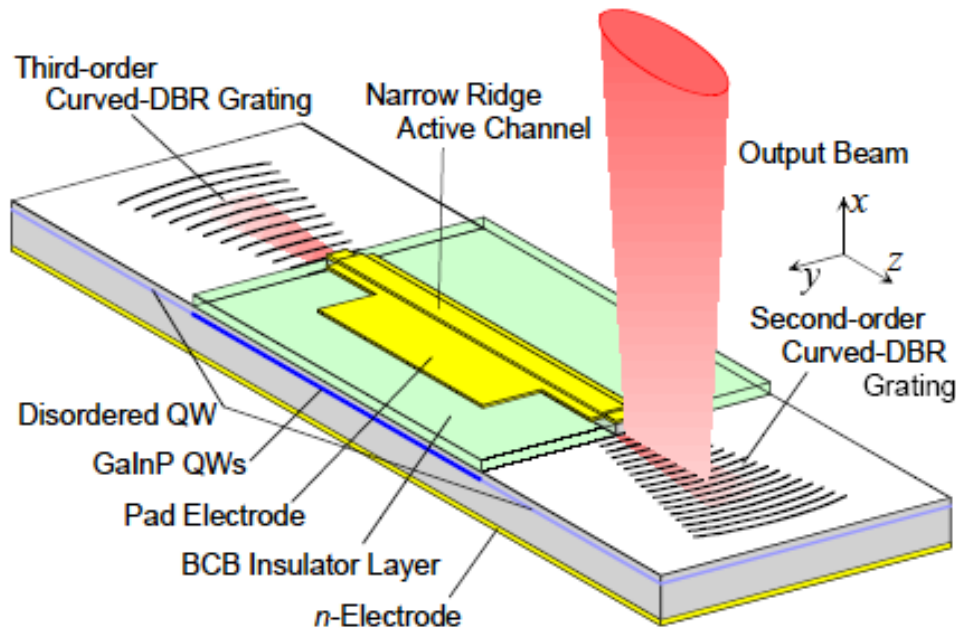
External Quantum Efficiency 74%

Side Mode Suppression 52 dB

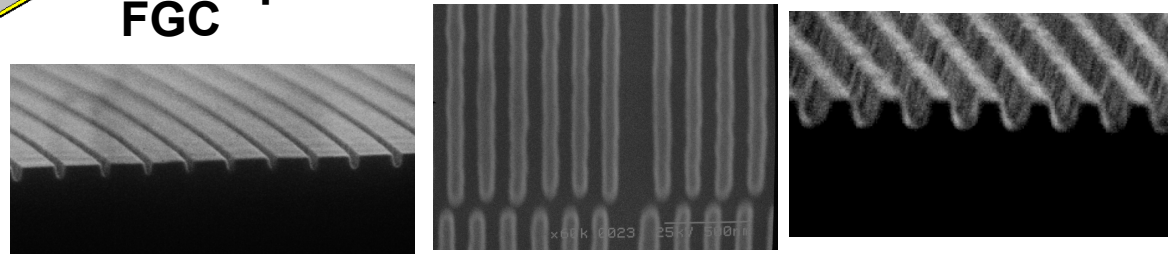
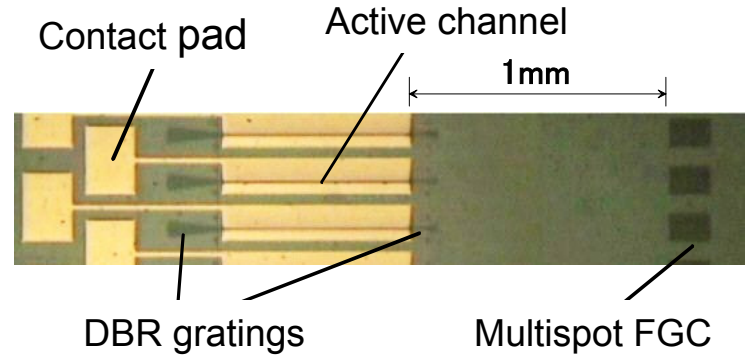
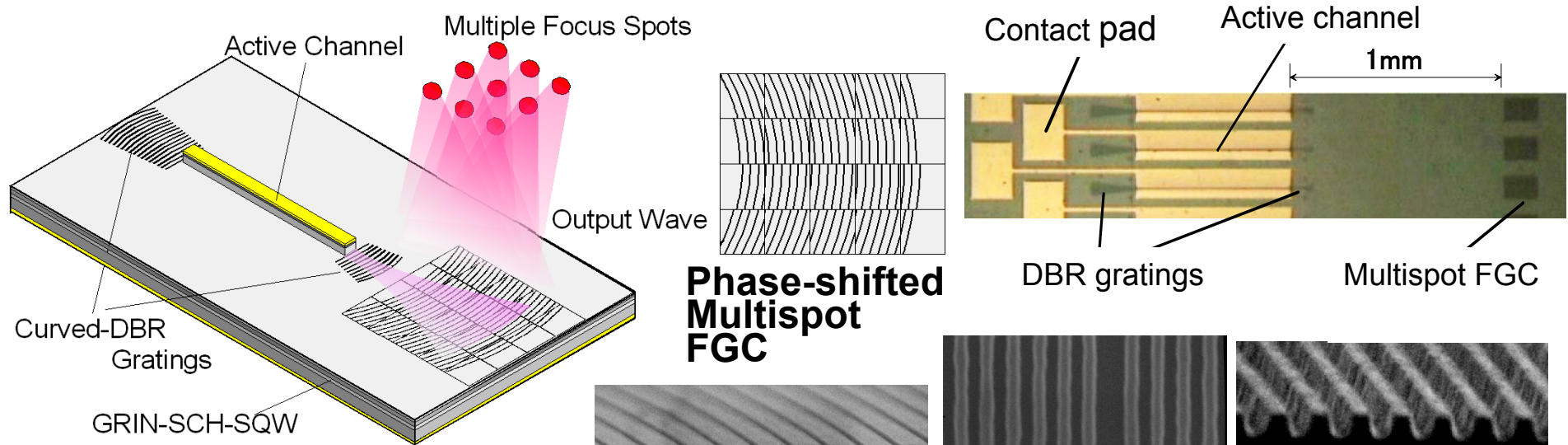
Maximum Output Power 250 mW

**Accomplished**

# Surface-Emitting Red DBR Laser and Application to Biomolecular Sensing

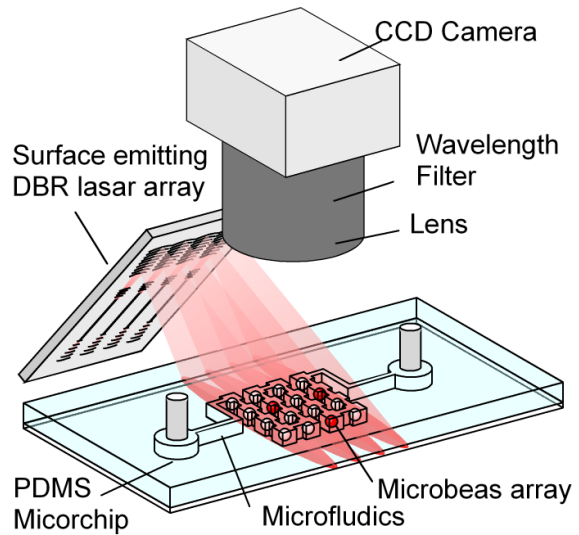


# DBR laser with multispot focusing grating coupler

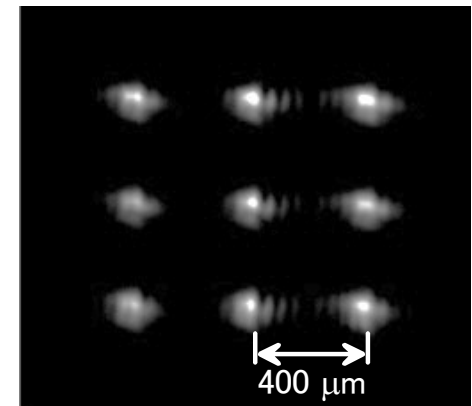
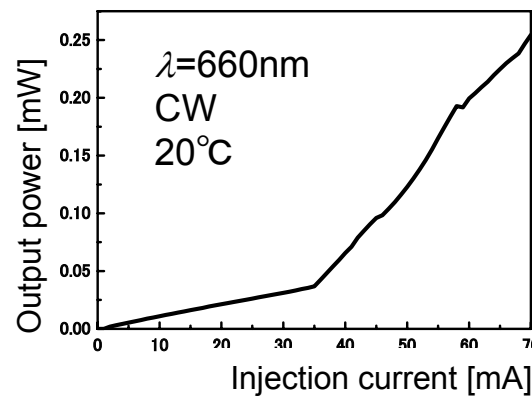


$\lambda \sim 191\text{nm}$

$d \sim 100\text{nm}$

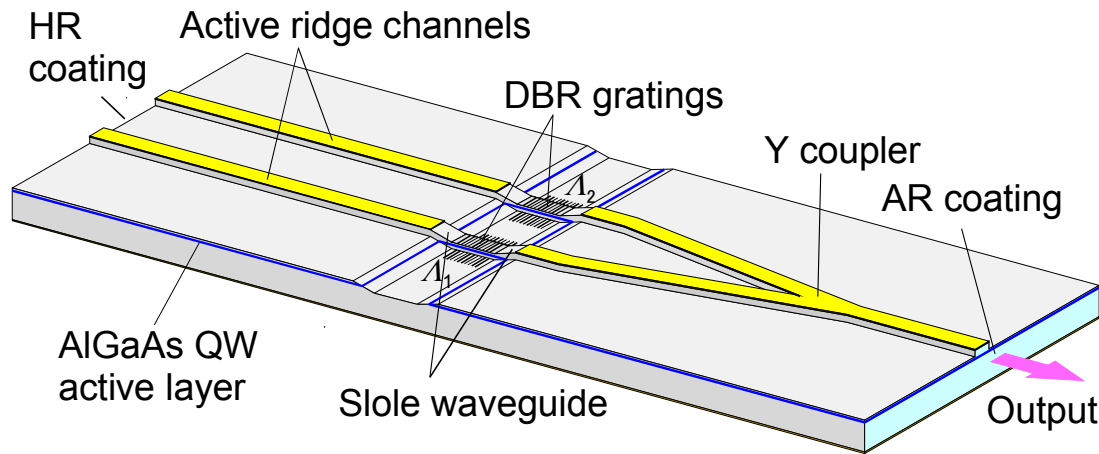


Application to biosensing



S.Takushima et al. JJAP 48, 030206, 2009

# Integrated twin DBR laser for THz wave generation



to GaAs photomixer

